

WHAT IS CLAIMED IS:

1. An electrode structure serving as a building component of an electron optical system array having a plurality of electron lenses, comprising:  
5 a substrate having a plurality of apertures for transmitting a plurality of charged-particle beams; and a plurality of electrodes extending from side surfaces of the plurality of apertures to peripheries  
10 of the plurality of apertures,  
wherein at least a surface of said substrate is insulated.

2. The structure according to claim 1, wherein the surface of said substrate has an insulating film.

15 3. The structure according to claim 1, wherein electrodes formed in at least two apertures are electrically connected.

4. The structure according to claim 1, wherein the plurality of apertures are arrayed, and  
20 electrodes formed in apertures of each column are electrically connected.

25 5. The structure according to claim 1, wherein the electrode structure further comprises an alignment portion for aligning the electrode structure with another electrode structure.

6. The structure according to claim 1, wherein said substrate includes a silicon substrate covered with an

insulating film after the plurality of apertures are formed.

7. An electron optical system array having a plurality of electron lenses, comprising a plurality of 5 electrode structures which are arranged along paths of a plurality of charged-particle beams and have pluralities of apertures on the paths of the plurality of charged-particle beams,

wherein at least one of said plurality of 10 electrode structures includes

a substrate having a plurality of apertures for transmitting the plurality of charged-particle beams, and

a plurality of electrodes extending from side 15 surfaces of the plurality of apertures to peripheries of the plurality of apertures, and  
at least a surface of said substrate is insulated.

8. The array according to claim 7, wherein the surface of said substrate has an insulating film.

20 9. The array according to claim 7, wherein electrodes formed in at least two apertures of said substrate are electrically connected.

10. The array according to claim 7, wherein the plurality of apertures of said plurality of 25 electrode structures are arrayed, and electrodes formed in each column of said substrate are electrically connected.

11. The array according to claim 7, wherein said plurality of electrode structures include a shield electrode structure.

12. The array according to claim 7, wherein  
5 each of said plurality of electrode structures comprises a membrane portion which has the plurality of apertures and a support portion which supports the membrane portion, and  
the electron optical system array further  
10 comprises a spacer interposed between support portions of adjacent electrode structures to define a distance between the support portions.

13. The array according to claim 7, wherein  
each of said plurality of electrode structures  
15 comprises a membrane portion in which the plurality of apertures are formed and a support portion which supports the membrane portion, and  
the electron optical system array further  
comprises a spacer interposed between membrane portions  
20 of adjacent electrode structures to define a distance between the membrane portions.

14. The array according to claim 7, wherein  
each of said plurality of electrode structures  
comprises a membrane portion which has the plurality of  
25 apertures and a support portion which supports the membrane portion, and  
the electron optical system array further

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comprises:

a first spacer interposed between support portions of adjacent electrode structures to define a distance between the support portions; and

5 a second spacer interposed between membrane portions of adjacent electrode structures to define a distance between the membrane portions.

15. A method of manufacturing an electrode structure serving as a building component of an electron optical system having a plurality of electron lenses,  
10 comprising the steps of:

forming in a substrate a plurality of apertures for transmitting a plurality of charged-particle beams;

covering the substrate having the plurality of apertures with an insulating film; and

15 forming, in the substrate covered with the insulating film, a plurality of electrodes extending from side surfaces of the plurality of apertures to peripheries of the plurality of apertures.

20 16. The method according to claim 15, wherein the substrate includes a silicon substrate, and in the step of forming a plurality of apertures, a plurality of apertures are formed in the silicon substrate by plasma dry etching.

25 17. A charged-particle beam exposure apparatus comprising:

a charged-particle beam source for emitting a

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charged-particle beam;

an electron optical system array which has a plurality of electron lenses and forms a plurality of intermediate images of said charged-particle beam

5 source by the plurality of electron lenses; and

a projection electron optical system for projecting on a substrate the plurality of intermediate images formed by said electron optical system array,

wherein said electron optical system array

10 includes a plurality of electrode structures which are arranged along paths of a plurality of charged-particle beams concerning the plurality of intermediate images and have pluralities of apertures on the paths of the plurality of charged-particle beams,

15 at least one of said plurality of electrode structures includes

a substrate having a plurality of apertures for transmitting the plurality of charged-particle beams, and

20 a plurality of electrodes extending from side surfaces of the plurality of apertures to peripheries of the plurality of apertures, and

at least a surface of said substrate is insulated.

18. A device manufacturing method comprising the

25 steps of:

installing a plurality of semiconductor manufacturing apparatuses including a charged-particle

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beam exposure apparatus in a factory; and  
manufacturing a semiconductor device by using the  
plurality of semiconductor manufacturing apparatuses,  
wherein the charged-particle beam exposure  
5 apparatus includes  
a charged-particle beam source for emitting a  
charged-particle beam,  
an electron optical system array which has a  
plurality of electron lenses and forms a plurality of  
10 intermediate images of the charged-particle beam source  
by the plurality of electron lenses, and  
a projection electron optical system for  
projecting on a substrate the plurality of intermediate  
images formed by the electron optical system array,  
15 the electron optical system array includes a  
plurality of electrode structures which are arranged  
along paths of a plurality of charged-particle beams  
concerning the plurality of intermediate images and  
have pluralities of apertures on the paths of the  
20 plurality of charged-particle beams,  
at least one of the plurality of electrode  
structures includes  
a substrate having a plurality of apertures for  
transmitting the plurality of charged-particle beams,  
25 and  
a plurality of electrodes extending from side  
surfaces of the plurality of apertures to peripheries

of the plurality of apertures, and  
at least a surface of the substrate is insulated.

19. The method according to claim 18, further  
comprising the steps of:

5 connecting the plurality of semiconductor  
manufacturing apparatuses by a local area network;  
connecting the local area network to an external  
network of the factory;

10 acquiring information about the charged-particle  
beam exposure apparatus from a database on the external  
network by using the local area network and the  
external network; and

controlling the charged-particle beam exposure  
apparatus on the basis of the acquired information.

15 20. A semiconductor manufacturing factory comprising:  
a plurality of semiconductor manufacturing  
apparatuses including a charged-particle beam exposure  
apparatus;

20 a local area network for connecting said  
plurality of semiconductor manufacturing apparatuses;  
and

a gateway for connecting the local area network  
to an external network of said semiconductor  
manufacturing factory,

25 wherein said charged-particle beam exposure  
apparatus includes

a charged-particle beam source for emitting a

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charged-particle beam,

an electron optical system array which has a plurality of electron lenses and forms a plurality of intermediate images of said charged-particle beam

5 source by the plurality of electron lenses, and

a projection electron optical system for projecting on a substrate the plurality of intermediate images formed by said electron optical system array,

said electron optical system array includes a

10 plurality of electrode structures which are arranged along paths of a plurality of charged-particle beams concerning the plurality of intermediate images and have pluralities of apertures on the paths of the plurality of charged-particle beams,

15 at least one of said plurality of electrode structures includes

a substrate having a plurality of apertures for transmitting the plurality of charged-particle beams, and

20 a plurality of electrodes extending from side surfaces of the plurality of apertures to peripheries of the plurality of apertures, and

at least a surface of said substrate is insulated.

21. A maintenance method for a charged-particle beam

25 exposure apparatus, comprising the steps of:

preparing a database for storing information about maintenance of the charged-particle beam exposure

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apparatus on an external network of a factory where the charged-particle beam exposure apparatus is installed;

connecting the charged-particle beam exposure apparatus to a local area network in the factory; and

5 maintaining the charged-particle beam exposure apparatus on the basis of the information stored in the database by using the external network and the local area network,

wherein the charged-particle beam exposure

10 apparatus includes

a charged-particle beam source for emitting a charged-particle beam,

an electron optical system array which has a plurality of electron lenses and forms a plurality of

15 intermediate images of the charged-particle beam source by the plurality of electron lenses, and

a projection electron optical system for projecting on a substrate the plurality of intermediate images formed by the electron optical system array,

20 the electron optical system array includes a plurality of electrode structures which are arranged along paths of a plurality of charged-particle beams concerning the plurality of intermediate images and have pluralities of apertures on the paths of the

25 plurality of charged-particle beams,

at least one of the plurality of electrode structures includes

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a substrate having a plurality of apertures for  
transmitting the plurality of charged-particle beams,  
and

5 a plurality of electrodes extending from side  
surfaces of the plurality of apertures to peripheries  
of the plurality of apertures, and  
at least a surface of the substrate is insulated.